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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	15
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 6x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	24-WFQFN Exposed Pad
Supplier Device Package	24-HWQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1007egna-u0

Table 1-1. List of Ordering Part Numbers

(3/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
			Note	
36 pins	36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)	Mounted	A G	R5F100CAALA#U0, R5F100CCALA#U0, R5F100CDALA#U0, R5F100CEALA#U0, R5F100CFALA#U0, R5F100CGALA#U0 R5F100CAALA#W0, R5F100CAALA#W0, R5F100CBALA#W0, R5F100CEALA#W0, R5F100CGALA#W0 R5F100CAGLA#W0 R5F100CAGLA#U0, R5F100CAGLA#U0, R5F100CBA#U0, R5F100CBA#U0 R5F100CAGLA#W0, R5F100CAGLA#W0 R5F100CAGLA#W0, R5F100CAGLA#W0, R5F100CAGLA#W0, R5F100CAGLA#W0, R5F100CAGLA#W0, R5F100CAGLA#W0, R5F100CAGLA#W0
		Not mounted	A	R5F101CAALA#U0, R5F101CCALA#U0, R5F101CDALA#U0, R5F101CEALA#U0, R5F101CFALA#U0, R5F101CGALA#U0 R5F101CAALA#W0, R5F101CCALA#W0, R5F101CDALA#W0,
40 pins	40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)	Mounted	A	R5F101CEALA#W0, R5F101CFALA#W0, R5F101CGALA#W0 R5F100EAANA#U0, R5F100ECANA#U0, R5F100EDANA#U0, R5F100EEANA#U0, R5F100EFANA#U0, R5F100EGANA#U0, R5F100EHANA#U0 R5F100EAANA#W0, R5F100ECANA#W0, R5F100EDANA#W0, R5F100EEANA#W0, R5F100EFANA#W0, R5F100EGANA#W0,
			D	R5F100EHANA#W0 R5F100EADNA#U0, R5F100ECDNA#U0, R5F100EDDNA#U0, R5F100EEDNA#U0, R5F100EFDNA#U0, R5F100EGDNA#U0, R5F100EHDNA#U0 R5F100EADNA#W0, R5F100ECDNA#W0, R5F100EDDNA#W0, R5F100EEDNA#W0, R5F100EFDNA#W0, R5F100EGDNA#W0, R5F100EHDNA#W0
			G	R5F100EAGNA#U0, R5F100ECGNA#U0, R5F100EDGNA#U0, R5F100EEGNA#U0, R5F100EFGNA#U0, R5F100EGGNA#U0, R5F100EHGNA#U0 R5F100EAGNA#W0, R5F100ECGNA#W0, R5F100EDGNA#W0, R5F100EEGNA#W0, R5F100EFGNA#W0, R5F100EFGNA#W0, R5F100EHGNA#W0
		Not mounted	A D	R5F101EAANA#U0, R5F101ECANA#U0, R5F101EDANA#U0, R5F101EEANA#U0, R5F101EFANA#U0, R5F101EGANA#U0, R5F101EHANA#U0 R5F101EAANA#W0, R5F101ECANA#W0, R5F101EDANA#W0, R5F101EEANA#W0, R5F101EGANA#W0, R5F101EHANA#W0 R5F101EHANA#W0 R5F101EADNA#U0, R5F101ECDNA#U0, R5F101EDDNA#U0, R5F101EEDNA#U0, R5F101EEDNA#U0, R5F101EEDNA#U0, R5F101EHDNA#U0 R5F101EADNA#W0, R5F101ECDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0, R5F101EDDNA#W0,

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



Table 1-1. List of Ordering Part Numbers

(6/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
48 pins	48-pin plastic	Mounted	А	R5F100GAANA#U0, R5F100GCANA#U0, R5F100GDANA#U0,
	HWQFN (7 $\times$ 7 mm,			R5F100GEANA#U0, R5F100GFANA#U0, R5F100GGANA#U0,
	0.5 mm pitch)			R5F100GHANA#U0, R5F100GJANA#U0, R5F100GKANA#U0,
				R5F100GLANA#U0
				R5F100GAANA#W0, R5F100GCANA#W0,
				R5F100GDANA#W0, R5F100GEANA#W0,
				R5F100GFANA#W0, R5F100GGANA#W0,
				R5F100GHANA#W0, R5F100GJANA#W0,
				R5F100GKANA#W0, R5F100GLANA#W0
			D	R5F100GADNA#U0, R5F100GCDNA#U0, R5F100GDDNA#U0,
				R5F100GEDNA#U0, R5F100GFDNA#U0, R5F100GGDNA#U0,
				R5F100GHDNA#U0, R5F100GJDNA#U0, R5F100GKDNA#U0,
				R5F100GLDNA#U0
				R5F100GADNA#W0, R5F100GCDNA#W0,
				R5F100GDDNA#W0, R5F100GEDNA#W0,
				R5F100GFDNA#W0, R5F100GGDNA#W0,
				R5F100GHDNA#W0, R5F100GJDNA#W0,
				R5F100GKDNA#W0, R5F100GLDNA#W0
			G	R5F100GAGNA#U0, R5F100GCGNA#U0, R5F100GDGNA#U0,
				R5F100GEGNA#U0, R5F100GFGNA#U0, R5F100GGGNA#U0,
				R5F100GHGNA#U0, R5F100GJGNA#U0
				R5F100GAGNA#W0, R5F100GCGNA#W0,
				R5F100GDGNA#W0, R5F100GEGNA#W0,
				R5F100GFGNA#W0, R5F100GGGNA#W0,
				R5F100GHGNA#W0, R5F100GJGNA#W0
		Not	Α	R5F101GAANA#U0, R5F101GCANA#U0, R5F101GDANA#U0,
		mounted		R5F101GEANA#U0, R5F101GFANA#U0, R5F101GGANA#U0,
				R5F101GHANA#U0, R5F101GJANA#U0, R5F101GKANA#U0,
				R5F101GLANA#U0
				R5F101GAANA#W0, R5F101GCANA#W0,
				R5F101GDANA#W0, R5F101GEANA#W0,
				R5F101GFANA#W0, R5F101GGANA#W0,
				R5F101GHANA#W0, R5F101GJANA#W0,
				R5F101GKANA#W0, R5F101GLANA#W0
			D	R5F101GADNA#U0, R5F101GCDNA#U0, R5F101GDDNA#U0,
				R5F101GEDNA#U0, R5F101GFDNA#U0, R5F101GGDNA#U0,
				R5F101GHDNA#U0, R5F101GJDNA#U0, R5F101GKDNA#U0,
				R5F101GLDNA#U0
				R5F101GADNA#W0, R5F101GCDNA#W0,
				R5F101GDDNA#W0, R5F101GEDNA#W0,
				R5F101GFDNA#W0, R5F101GGDNA#W0,
				R5F101GHDNA#W0, R5F101GJDNA#W0,
				R5F101GKDNA#W0, R5F101GLDNA#W0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

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Table 1-1. List of Ordering Part Numbers

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Pin count	Package	Data flash	Fields of	Ordering Part Number
			Application Note	
64 pins	64-pin plastic LQFP	Mounted	Α	R5F100LCAFA#V0, R5F100LDAFA#V0,
	(12 × 12 mm, 0.65			R5F100LEAFA#V0, R5F100LFAFA#V0,
	mm pitch)			R5F100LGAFA#V0, R5F100LHAFA#V0,
				R5F100LJAFA#V0, R5F100LKAFA#V0, R5F100LLAFA#V0
				R5F100LCAFA#X0, R5F100LDAFA#X0,
				R5F100LEAFA#X0, R5F100LFAFA#X0,
			D	R5F100LGAFA#X0, R5F100LHAFA#X0,
				R5F100LJAFA#X0, R5F100LKAFA#X0, R5F100LLAFA#X0
				R5F100LCDFA#V0, R5F100LDDFA#V0,
				R5F100LEDFA#V0, R5F100LFDFA#V0,
				R5F100LGDFA#V0, R5F100LHDFA#V0,
				R5F100LJDFA#V0, R5F100LKDFA#V0, R5F100LLDFA#V0
			G	R5F100LCDFA#X0, R5F100LDDFA#X0,
				R5F100LEDFA#X0, R5F100LFDFA#X0,
				R5F100LGDFA#X0, R5F100LHDFA#X0,
				R5F100LJDFA#X0, R5F100LKDFA#X0, R5F100LLDFA#X0
				R5F100LCGFA#V0, R5F100LDGFA#V0,
				R5F100LEGFA#V0, R5F100LFGFA#V0
				R5F100LCGFA#X0, R5F100LDGFA#X0,
				R5F100LEGFA#X0, R5F100LFGFA#X0
				R5F100LGGFA#V0, R5F100LHGFA#V0,
				R5F100LJGFA#V0
				R5F100LGGFA#X0, R5F100LHGFA#X0,
				R5F100LJGFA#X0
		Not	Α	R5F101LCAFA#V0, R5F101LDAFA#V0,
		mounted		R5F101LEAFA#V0, R5F101LFAFA#V0,
				R5F101LGAFA#V0, R5F101LHAFA#V0,
				R5F101LJAFA#V0, R5F101LKAFA#V0, R5F101LLAFA#V0
				R5F101LCAFA#X0, R5F101LDAFA#X0,
				R5F101LEAFA#X0, R5F101LFAFA#X0,
			D	R5F101LGAFA#X0, R5F101LHAFA#X0,
				R5F101LJAFA#X0, R5F101LKAFA#X0, R5F101LLAFA#X0
				R5F101LCDFA#V0, R5F101LDDFA#V0,
				R5F101LEDFA#V0, R5F101LFDFA#V0,
				R5F101LGDFA#V0, R5F101LHDFA#V0,
				R5F101LJDFA#V0, R5F101LKDFA#V0, R5F101LLDFA#V0
				R5F101LCDFA#X0, R5F101LDDFA#X0,
				R5F101LEDFA#X0, R5F101LFDFA#X0,
				R5F101LGDFA#X0, R5F101LHDFA#X0,
				R5F101LJDFA#X0, R5F101LKDFA#X0, R5F101LLDFA#X0

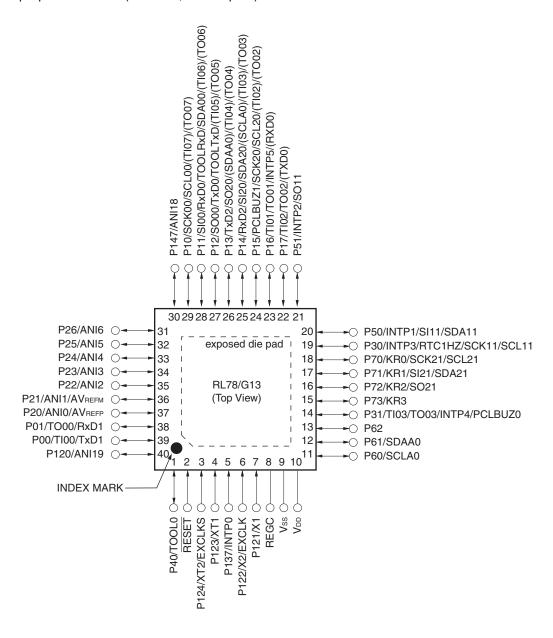
Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



### 1.3.7 40-pin products

• 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)



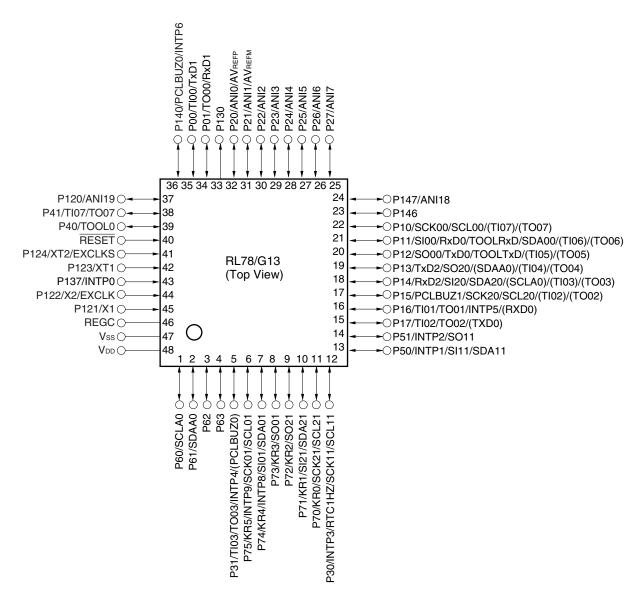
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to Vss.

### 1.3.9 48-pin products

• 48-pin plastic LFQFP (7 x 7 mm, 0.5 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

		I		l			(1/2)		
	Item	80-		100-pin		128			
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx		
Code flash me	emory (KB)	96 to	512	96 to	o 512	192 t	o 512		
Data flash me	mory (KB)	8	-	8	_	8	_		
RAM (KB)		8 to 3	2 Note 1	8 to 3	32 Note 1	16 to 3	32 Note 1		
Address spac	e	1 MB							
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V <sub>DD</sub> = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V <sub>DD</sub> = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V <sub>DD</sub> = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V <sub>DD</sub> = 1.6 to 5.5 V)							
	High-speed on-chip oscillator	HS (High-speed LS (Low-speed	l main) mode: 1 main) mode: 1	to 32 MHz (V <sub>DD</sub> = to 16 MHz (V <sub>DD</sub> = to 8 MHz (V <sub>DD</sub> = to 4 MHz (V <sub>DD</sub> =	= 2.4 to 5.5 V), 1.8 to 5.5 V),				
Subsystem clo	ock	XT1 (crystal) os 32.768 kHz	cillation, externa	l subsystem cloc	k input (EXCLKS	)			
Low-speed on	n-chip oscillator	15 kHz (TYP.)							
General-purpo	ose register	(8-bit register × 8) × 4 banks							
Minimum instr	ruction execution time	0.03125 $\mu$ s (High-speed on-chip oscillator: f <sub>IH</sub> = 32 MHz operation)							
		0.05 µs (High-speed system clock: fmx = 20 MHz operation)							
		30.5 μs (Subsystem clock: fsuB = 32.768 kHz operation)							
Instruction set	t	<ul> <li>Data transfer (8/16 bits)</li> <li>Adder and subtractor/logical operation (8/16 bits)</li> <li>Multiplication (8 bits × 8 bits)</li> <li>Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.</li> </ul>							
I/O port	Total	7	'4	ę	92	1:	20		
	CMOS I/O	(N-ch O.D. I/O	64 [EV <sub>DD</sub> withstand re]: 21)	(N-ch O.D. I/O	32 [EV <sub>DD</sub> withstand ge]: 24)	(N-ch O.D. I/O	10 [EV <sub>DD</sub> withstand e]: 25)		
	CMOS input		5		5		5		
	CMOS output		1		1		1		
	N-ch O.D. I/O (withstand voltage: 6 V)		4		4		4		
Timer	16-bit timer	12 cha	annels	12 cha	annels	16 cha	nnels		
	Watchdog timer	1 cha	annel	1 cha	annel	1 cha	nnel		
	Real-time clock (RTC)	1 cha	annel	1 cha	annel	1 cha	nnel		
	12-bit interval timer (IT)	1 cha	annel	1 cha	annel	1 cha	nnel		
	Timer output	12 channels (PWM outputs:	10 Note 2)	12 channels (PWM outputs:	10 Note 2)	16 channels (PWM outputs:	14 Note 2)		
	RTC output	1 channel • 1 Hz (subsyst	tem clock: fsuв =	32.768 kHz)					

**Notes 1.** The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$  (2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low <sup>Note 1</sup>	lo <sub>L1</sub>	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147				20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145 (When duty $\leq$ 70% Note 3) Total of P05, P06, P10 to P17, P30,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			70.0	mA
			$2.7~V \leq EV_{DD0} < 4.0~V$			15.0	mA
			$1.8~V \leq EV_{DD0} < 2.7~V$			9.0	mA
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			4.5	mA
			$4.0~V \leq EV_{DD0} \leq 5.5~V$			80.0	mA
		P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97.	$2.7~V \leq EV_{DD0} < 4.0~V$			35.0	mA
		P100, P101, P110 to P117, P146,	$1.8~V \leq EV_{DD0} < 2.7~V$			20.0	mA
			$1.6~V \le EV_{DD0} < 1.8~V$			10.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				150.0	mA
	lo <sub>L2</sub>	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	$1.6~V \leq V_{DD} \leq 5.5~V$			5.0	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1 and Vss pin.
  - 2. However, do not exceed the total current value.
  - **3.** Specification under conditions where the duty factor  $\leq 70\%$ .

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins =  $(lol \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and lol = 10.0 mA

Total output current of pins =  $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$  mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
  - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
  - 3. When high-speed system clock and subsystem clock are stopped.
  - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
  - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

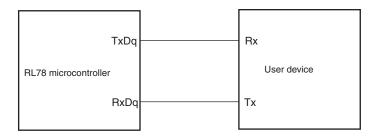
HS (high-speed main) mode:  $2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$  to 32 MHz

 $2.4~V \le V_{DD} \le 5.5~V @ 1~MHz$  to 16~MHz

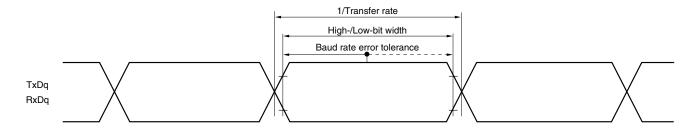
LS (low-speed main) mode: 1.8 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V@1 MHz to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
  - 2. fih: High-speed on-chip oscillator clock frequency
  - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
  - 4. Except subsystem clock operation, temperature condition of the TYP. value is T<sub>A</sub> = 25°C

### **UART** mode connection diagram (during communication at same potential)



### **UART** mode bit width (during communication at same potential) (reference)



**Remarks 1.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

2. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10 to 13))

# (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/2)$ 

Parameter	Symbol	Conditions		HS (	high- main) ode	LS (low		-	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1		$4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}$	24 MHz < fmck	14/ fмск		_		_		ns
			20 MHz < fмcκ ≤ 24 MHz	12/ fмск						ns
			8 MHz < fмcк ≤ 20 MHz	10/ fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/ fмск		_		ns
			fmck ≤ 4 MHz	6/fмск		10/ fмск		10/ fмск		ns
		$2.7 \text{ V} \le \text{EV}_{DD0} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$	24 MHz < fмск	20/ fмск		_		_		ns
			20 MHz < fмcк ≤ 24 MHz	16/ fмск		_		_		ns
			16 MHz < fмcк ≤ 20 MHz	14/ fмск		_		_		ns
			8 MHz < fмcк ≤ 16 MHz	12/ fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/ fмск		_		ns
			fмск ≤ 4 MHz	6/ƒмск		10/ fмск		10/ fмск		ns
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note}}$	24 MHz < fмск	48/ fмск		_		_		ns
		2	20 MHz < fмcк ≤ 24 MHz	36/ fмск		_		_		ns
			16 MHz < fмcк ≤ 20 MHz	32/ fмск		_		_		ns
			8 MHz < f <sub>MCK</sub> ≤ 16 MHz	26/ fмск						ns
			4 MHz < f <sub>MCK</sub> ≤ 8 MHz	16/ fмск		16/ fмск		_		ns
			fмcк ≤ 4 MHz	10/ fмск		10/ fмск		10/ fмск		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

- **6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter is in operation.
- 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- 8. Current flowing only during data flash rewrite.
- **9.** Current flowing only during self programming.
- 10. For shift time to the SNOOZE mode, see 18.3.3 SNOOZE mode in the RL78/G13 User's Manual.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
  - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
  - 3. fclk: CPU/peripheral hardware clock frequency
  - **4.** Temperature condition of the TYP. value is  $T_A = 25^{\circ}C$



### (4) During communication at same potential (simplified I<sup>2</sup>C mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	HS (high-speed main)  Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$2.7~V \leq EV_{DD0} \leq 5.5~V,$		400 Note1	kHz
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$		100 Note1	kHz
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "L"	tLOW	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	1200		ns
		$C_b = 50$ pF, $R_b = 2.7$ k $\Omega$			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "H"	tніgн	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	1200		ns
		$C_b = 50$ pF, $R_b = 2.7$ k $\Omega$			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Data setup time (reception)	tsu:dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	1/fmck + 220		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	Note2		
		$2.4~V \leq EV_{DD} \leq 5.5~V,$	1/fmck + 580		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	Note2		
Data hold time (transmission)	thd:dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	0	770	ns
		$C_b = 50$ pF, $R_b = 2.7$ k $\Omega$			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$	0	1420	ns
		$C_b = 100 \ pF, \ R_b = 3 \ k\Omega$			

Notes 1. The value must also be equal to or less than fmck/4.

2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (V<sub>DD</sub> tolerance (for the 20- to 52-pin products)/EV<sub>DD</sub> tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

#### (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ 

Parameter	Symbol	Conditions		Conditions HS (high-speed ma Mode		. ,	Unit
					MIN.	MAX.	
Transfer rate		Reception	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$			fmck/12 Note 1	bps
			$V$ , $2.7 \ V \le V_b \le 4.0 \ V$	Theoretical value of the maximum transfer rate fclk = 32 MHz, fmck = fclk		2.6	Mbps
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0$			fmck/12 Note 1	bps
	$\begin{array}{c} V,\\ 2.3\ V \leq V_{b} \end{array}$	$V,$ $2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate fclk = 32 MHz, fmck = fclk		2.6	Mbps	
			$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V},$			fMCK/12 Notes 1,2	bps
			$1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate fclk = 32 MHz, fmck = fclk		2.6	Mbps

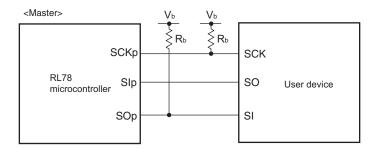
- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
  - 2. The following conditions are required for low voltage interface when EVDDO < VDD.

 $2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$ : MAX. 1.3 Mbps

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

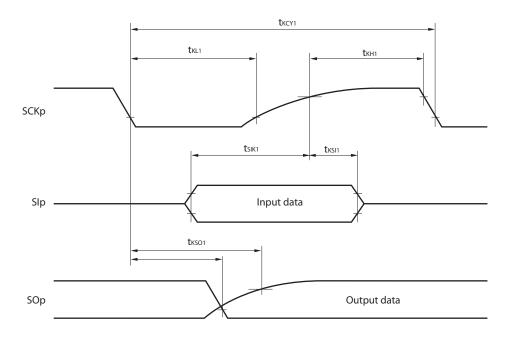
- Remarks 1. V<sub>b</sub>[V]: Communication line voltage
  - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
  - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10 to 13)
  - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

#### CSI mode connection diagram (during communication at different potential)

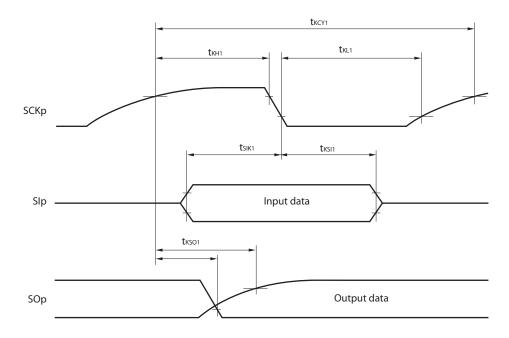


- Remarks 1.  $R_b[\Omega]$ :Communication line (SCKp, SOp) pull-up resistance,  $C_b[F]$ : Communication line (SCKp, SOp) load capacitance,  $V_b[V]$ : Communication line voltage
  - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
  - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
  - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

# CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



### CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 00, 01, 02, 10, 12, 13), n: Channel number (n = 0, 2), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

**2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

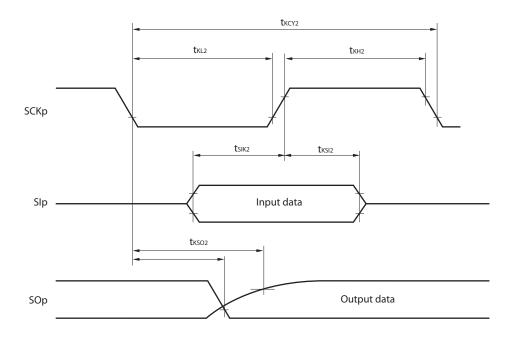
### (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ 

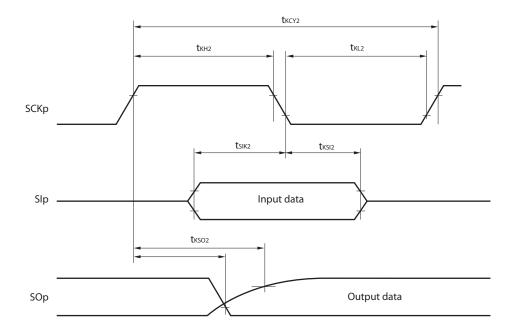
Parameter	Symbol	C	Conditions	HS (high-spe	ed main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 1	tkCY2	$4.0~V \leq EV_{DD0} \leq 5.5$	24 MHz < fмск	28/fмск		ns
		V,	20 MHz < fмcк ≤ 24 MHz	24/fмск		ns
		$2.7~V \leq V_b \leq 4.0~V$	8 MHz < fмcк ≤ 20 MHz	20/fмск		ns
			4 MHz < fmck ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
		$2.7~V \leq EV_{DD0} < 4.0$	24 MHz < fмск	40/fмск		ns
		V,	$20~\text{MHz} < \text{fmck} \le 24~\text{MHz}$	32/fмск		ns
		$2.3~V \leq V_b \leq 2.7~V$	16 MHz < fмcк ≤ 20 MHz	28/fмск		ns
			8 MHz < fмcк ≤ 16 MHz	24/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
		$2.4~V \leq EV_{DD0} < 3.3$	24 MHz < fмск	96/fмск		ns
		V,	20 MHz < fмcк ≤ 24 MHz	72/fмск		ns
		$1.6 \ V \le V_b \le 2.0 \ V$	16 MHz < fмcк ≤ 20 MHz	64/fмск		ns
			8 MHz < fмcк ≤ 16 MHz	52/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	32/fмск		ns
			fмcк ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level width	tкн2, tкL2	$4.0 \ V \le EV_{DD0} \le 5.$ $2.7 \ V \le V_b \le 4.0 \ V$	5 V,	tkcy2/2 - 24		ns
		$ 2.7 \ V \le EV_{DD0} < 4.0 \ V, $ $ 2.3 \ V \le V_b \le 2.7 \ V $		tkcy2/2 - 36		ns
		$2.4 \ V \le EV_{DD0} < 3.$ $1.6 \ V \le V_b \le 2.0 \ V$		tkcy2/2 - 100		ns
SIp setup time (to SCKp↑) Note2	tsık2	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 $ $ 2.7 \ V \leq V_b \leq 4.0 \ V $	5 V,	1/fмск + 40		ns
		$2.7 \ V \le EV_{DD0} < 4.$ $2.3 \ V \le V_b \le 2.7 \ V$	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			ns
		$2.4 \ V \le EV_{DD0} < 3.$ $1.6 \ V \le V_b \le 2.0 \ V$	3 V,	1/fмск + 60		ns
Slp hold time (from SCKp <sup>↑</sup> ) Note 3	tksi2			1/fmck + 62		ns
Delay time from SCKp↓ to SOp output Note 4	<b>t</b> KSO2	$4.0~V \leq EV_{DD0} \leq 5.$ $C_b = 30~pF,~R_b = 1$	5 V, 2.7 V $\leq$ V <sub>b</sub> $\leq$ 4.0 V, .4 k $\Omega$		2/fмск + 240	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2$	0 V, 2.3 V $\leq$ V <sub>b</sub> $\leq$ 2.7 V, .7 kΩ		2/fмск + 428	ns
		$2.4 \ V \le EV_{DD0} < 3.$ $C_b = 30 \ pF, \ R_b = 5$	3 V, 1.6 V ≤ V <sub>b</sub> ≤ 2.0 V .5 kΩ		2/fмск + 1146	ns

(Notes, Caution and Remarks are listed on the next page.)

# CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



### CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

**2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

- **Notes 1.** Excludes quantization error (±1/2 LSB).
  - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
  - **3.** When  $AV_{REFP} < V_{DD}$ , the MAX. values are as follows.

Overall error: Add  $\pm 1.0$  LSB to the MAX. value when AV<sub>REFP</sub> =  $V_{DD}$ .

Zero-scale error/Full-scale error: Add  $\pm 0.05\% FSR$  to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>.

Integral linearity error/ Differential linearity error: Add  $\pm 0.5$  LSB to the MAX. value when AV<sub>REFP</sub> = V<sub>DD</sub>.

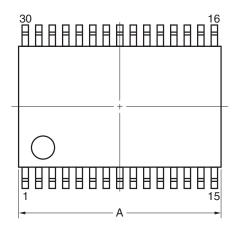
4. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

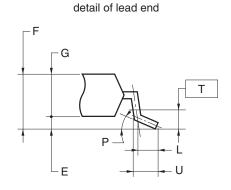


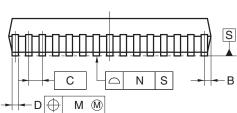
### 4.4 30-pin Products

R5F100AAASP, R5F100ACASP, R5F100ADASP, R5F100AEASP, R5F100AFASP, R5F100AGASP R5F101AAASP, R5F101ACASP, R5F101ADASP, R5F101AEASP, R5F101AFASP, R5F101AGASP R5F100AADSP, R5F100ACDSP, R5F100ADDSP, R5F100AEDSP, R5F100AFDSP, R5F100AGDSP R5F101AADSP, R5F101ACDSP, R5F101ADDSP, R5F101AEDSP, R5F101AFDSP, R5F101AGDSP R5F100AAGSP, R5F100ACGSP, R5F100ADGSP,R5F100AEGSP, R5F100AFGSP, R5F100AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18

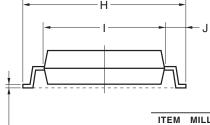






#### NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.



ITEM	MILLIMETERS
Α	9.85±0.15
В	0.45 MAX.
С	0.65 (T.P.)
D	$0.24^{+0.08}_{-0.07}$
Е	0.1±0.05
F	1.3±0.1
G	1.2
Н	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
М	0.13
N	0.10
Р	3°+5°
Т	0.25
U	0.6±0.15
	·

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			Description
Rev.	Date	Page	Summary
3.00	Aug 02, 2013	81	Modification of figure of AC Timing Test Points
		81	Modification of description and note 3 in (1) During communication at same potential (UART mode)
		83	Modification of description in (2) During communication at same potential (CSI mode)
		84	Modification of description in (3) During communication at same potential (CSI mode)
		85	Modification of description in (4) During communication at same potential (CSI mode) (1/2)
		86	Modification of description in (4) During communication at same potential (CSI mode) (2/2)
		88	Modification of table in (5) During communication at same potential (simplified I <sup>2</sup> C mode) (1/2)
		89	Modification of table and caution in (5) During communication at same potential (simplified I <sup>2</sup> C mode) (2/2)
		91	Modification of table and notes 1 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		92, 93	Modification of table and notes 2 to 7 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		94	Modification of remarks 1 to 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		95	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (1/2)
		96	Modification of table and caution in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (2/2)
		97	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		98	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		99	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		100	Modification of remarks 3 and 4 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		102	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/2)
		103	Modification of table and caution in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/2)
		106	Modification of table in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I <sup>2</sup> C mode) (1/2)
		107	Modification of table, note 1, and caution in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I <sup>2</sup> C mode) (2/2)
		109	Addition of (1) I <sup>2</sup> C standard mode
		111	Addition of (2) I <sup>2</sup> C fast mode
		112	Addition of (3) I <sup>2</sup> C fast mode plus
		112	Modification of IICA serial transfer timing
		113	Addition of table in 2.6.1 A/D converter characteristics
		113	Modification of description in 2.6.1 (1)
		114	Modification of notes 3 to 5 in 2.6.1 (1)
		115	Modification of description and notes 2, 4, and 5 in 2.6.1 (2)
		116	Modification of description and notes 3 and 4 in 2.6.1 (3)
		117	Modification of description and notes 3 and 4 in 2.6.1 (4)